

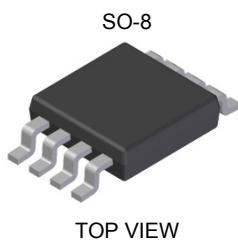
Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
20V	8m Ω @ $V_{GS} = 10\text{V}$	12A
	9m Ω @ $V_{GS} = 4.5\text{V}$	10A
	12m Ω @ $V_{GS} = 2.5\text{V}$	8A

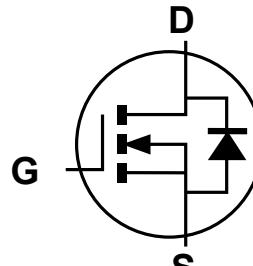
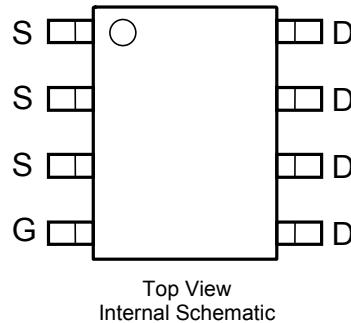
Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters



TOP VIEW



Equivalent circuit

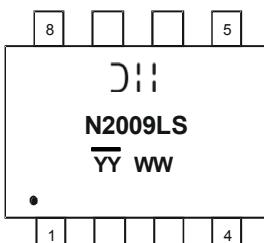
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2009LSS-13	SO-8	2500/Tape & Reel

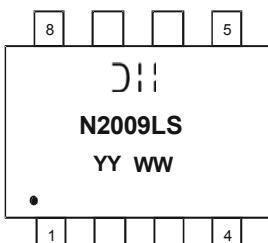
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

○ = Manufacturer's Marking
 N2009LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	± 12	V
Drain Current (Note 5)	Steady State	I_D	12 9.6	A
Pulsed Drain Current (Note 6)		I_{DM}	42	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2	W
Thermal Resistance, Junction to Ambient	R_{JJA}	62.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

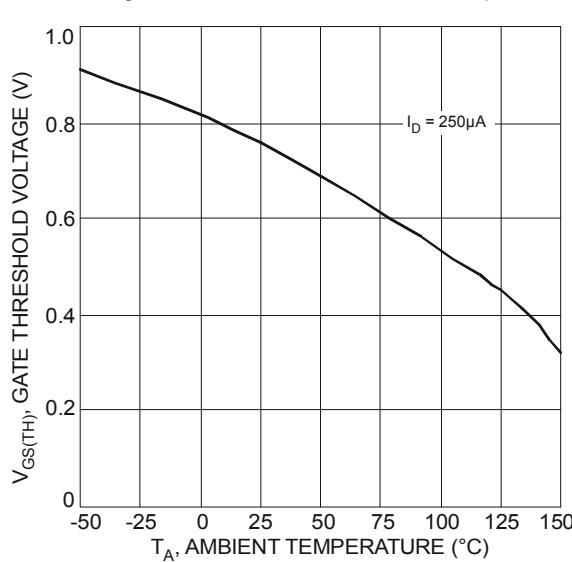
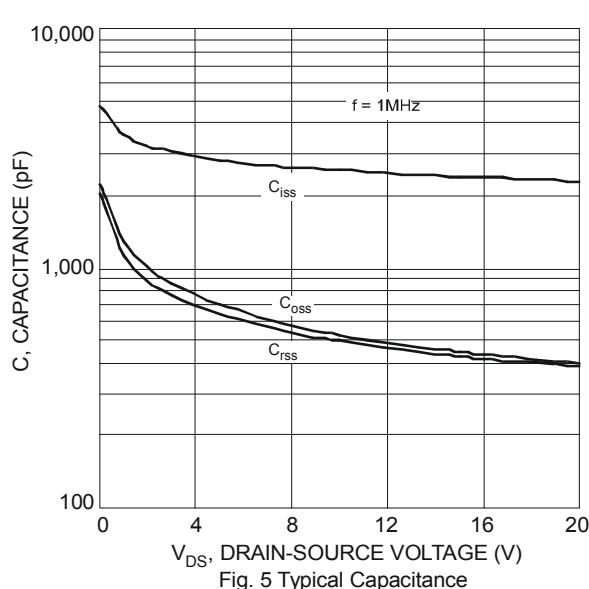
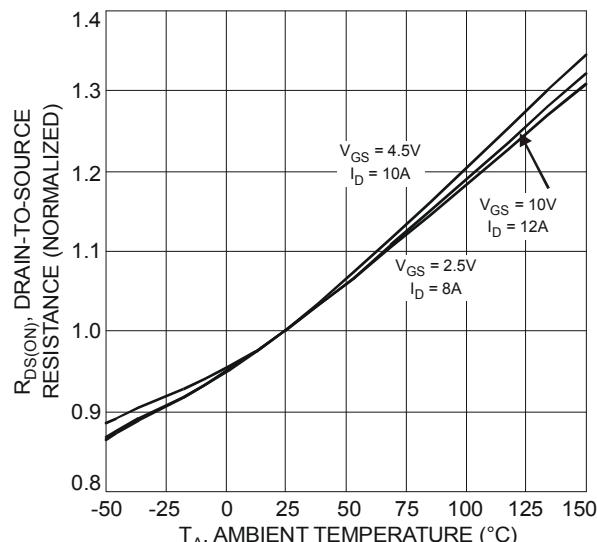
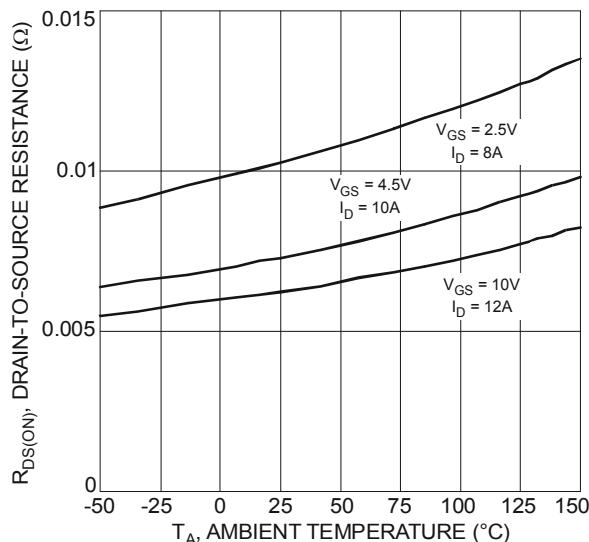
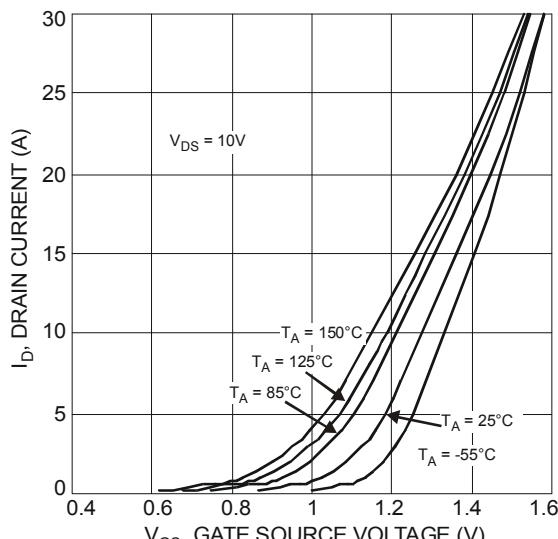
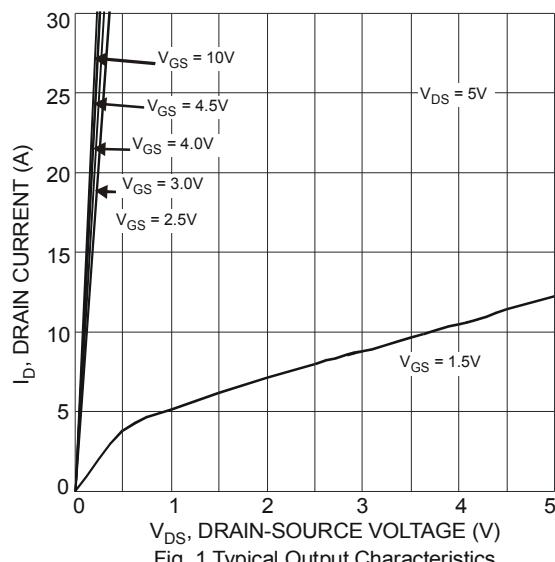
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	—	8 9 12	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 12\text{A}$ $V_{GS} = 4.5\text{V}, I_D = 10\text{A}$ $V_{GS} = 2.5\text{V}, I_D = 8\text{A}$
Forward Transconductance	g_{fs}	—	27	—	S	$V_{DS} = 5\text{V}, I_D = 6.5\text{A}$
Diode Forward Voltage	V_{SD}	0.5	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 3\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	2555	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	523	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	496	—	pF	
Gate Resistance	R_G	—	1.1	—	Ω	
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_g	—	28.9 58.3	—	nC	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 12\text{A}$ $V_{DS} = 10\text{V}, V_{GS} = 10\text{V}, I_D = 12\text{A}$
Gate-Source Charge	Q_{gs}	—	3.7	—		$V_{DS} = 10\text{V}, V_{GS} = 10\text{V}, I_D = 12\text{A}$
Gate-Drain Charge	Q_{gd}	—	11.4	—		$V_{DS} = 10\text{V}, V_{GS} = 10\text{V}, I_D = 12\text{A}$

Notes: 5. Device mounted on 2 oz, FR-4 PCB, with $R_{JJA} = 62.5^\circ\text{C}/\text{W}$

6. Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



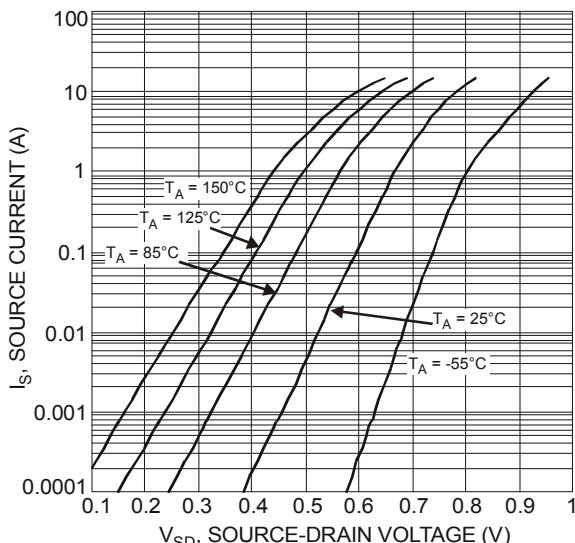


Fig. 7 Diode Forward Voltage vs. Current

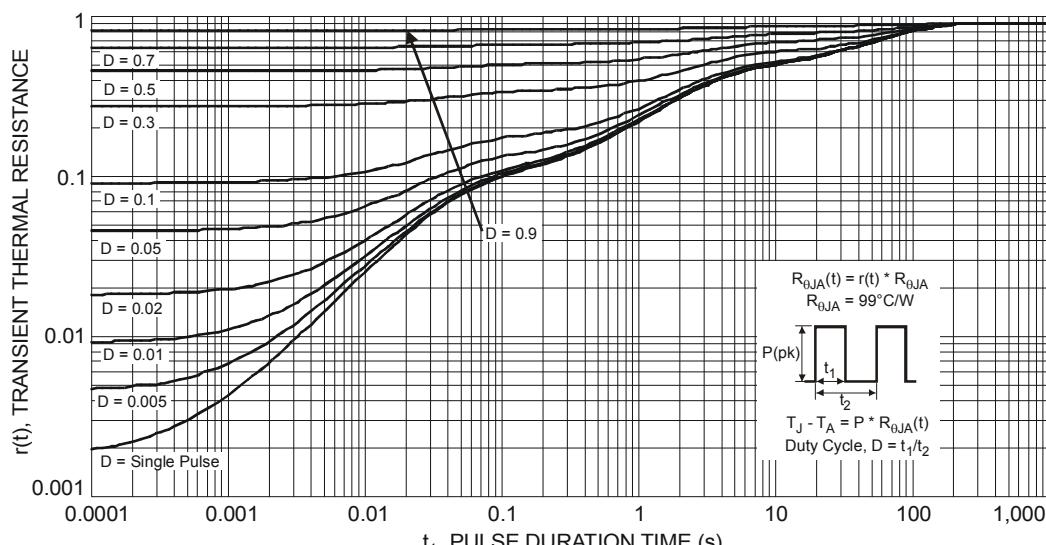
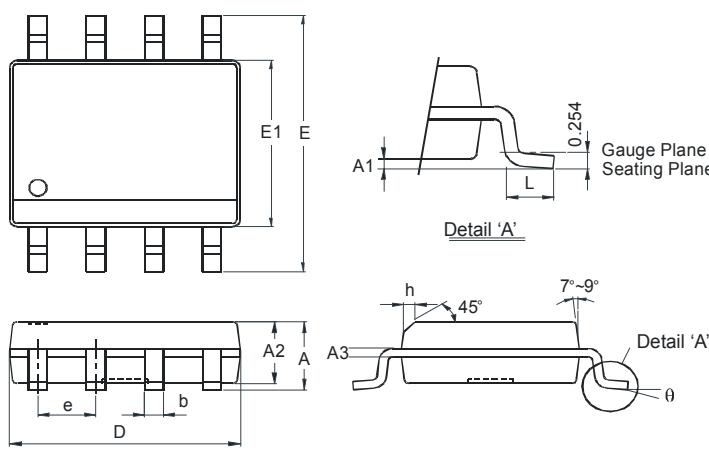


Fig. 8 Transient Thermal Response

Package Outline Dimensions

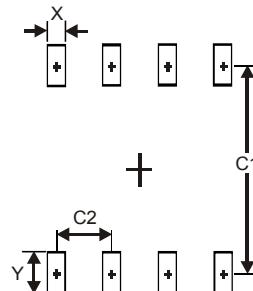
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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